

# Cyntec Automotive Solution for xEV

# Automotive World Tokyo 2023



25-27 Jan  
東京ビッグサイト  
Booth 41-24



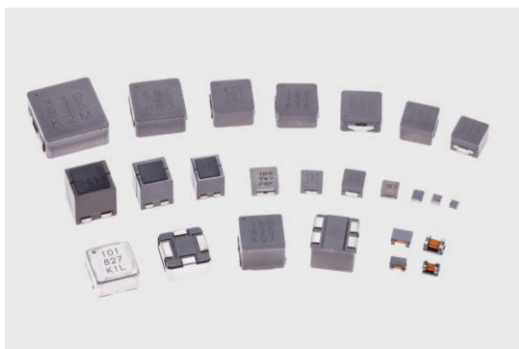
## Cyntec's Key Highlights @ Automotive World 2023



- ✓ Transformers
- ✓ Power chokes
- ✓ For on-board charger and DC/DC converters



- ✓ High accuracy shunt sensors
- ✓ ASIL-D qualified shunt sensor modules
- ✓ For battery management system



- ✓ Power chokes
- ✓ Common mode chokes
- ✓ LAN transformer
- ✓ For infotainment / ADAS / lighting ECUs



- ✓ Highly integrated, miniaturized automotive-grade DC-DC modules for ECUs



# Shunt Sensor & Shunt Sensor Module for BMS

Modularization



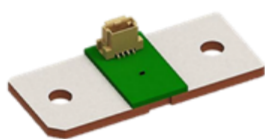
## Shunt Sensor



- w/ pin or w/o pin
- Patent pin implementation technology
- Robustness, high precision pin pitch



## Shunt Sensor with connector



- Precision can reach  $\leq \pm 0.5\%$  through temperature compensation
- Through QR code to reduce customer test loading



## Shunt Module with connector, A/D and MCU



- Optional design for customer selection
- Self-diagnostic capability to achieve ASIL level
- High accuracy level  $\pm 0.1\%$  by temperature compensation

## Technology Advantages



### Modular Design Competence

Modular design and bending busbar replaces most components reducing complexity and system cost. It also resettable after high energy fault.



### Thermal management

Professional team for heat distribution and structure design. Combine with high tech heat dissipated material and two phase cooling way.



### Accuracy

High accuracy level  $\leq \pm 0.1\%$  of voltage and current by temperature compensation through our calibration capabilities on shunt module.



### Safety

Design compatible of System, progress, product certificate of ISO26262. Semiconductor of SSR to meet shorter fault current cut-off time from ms to us



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## Shunt Sensor Family (Bus-bar type)



Chip Size (mil)	Chip Size (mm)	Operation Temp (°C)	Watt (W)	Tolerance (%)	Resistance Distribution
272*71	69*18	-65~170	36	5	25μΩ ← 50μΩ ← 100μΩ ← 150μΩ
330*79	84*20	-65~170	36	5	
330*142	84*36	-65~170	36	5	

TCR Range: ≤200ppm, ≤150ppm, ≤100ppm  
 Low TCR Range: ≤50ppm



## Shunt Sensor Family (Connector type)

Chip Size (mil)	Chip Size (mm)	Operation Temp (°C)	Nominal / Peak Current (A)	Tolerance (%)	Resistance Distribution
272*71	69*18*3	-65~125	500 / 1200 (5sec)	5	25μΩ ← 50μΩ ← 100μΩ ← 150μΩ
330*79	84*20*3	-65~125	600 / 1500 (5sec)	5	
330*142	84*36*3	-65~125	800 / 2000 (5sec)	5	

TCR Range: ≤200ppm, ≤150ppm, ≤100ppm

## ASIL C Shunt Module



- Nominal Input Voltage : 12~24V
- Current consumption : < 100mA
- Nominal Current : ±1500A
- Peak Current Measurement Range : ±4000A
- Primary Channel Accuracy : ± 0.1%
- Primary Channel Output : CAN
- >3 kV Galvanic Isolation.
- ISO16750 Part 2, Electrical loads for 24V
- Wide Operating temperature range: -40~105°C

## ASIL D Shunt Module



- Nominal Input Voltage : 12~24V
- Nominal Current : ±1000A
- Peak Current Measurement Range : ±10000A (Period: 10ms)
- Primary Channel Accuracy : ± 0.1%
- Secondary Channel(Analog) Accuracy : 2%
- Primary Channel Output : Digital \_ CAN FD
- Secondary Channel Output : Analog \_ 0 ~ 5V.
- >3 kV Galvanic Isolation.
- ISO16750 Part 2, Electrical loads for 24V

### More Spec Information

Shunt Sensor: [Click here](#)

Shunt Sensor Module: [Click here](#)

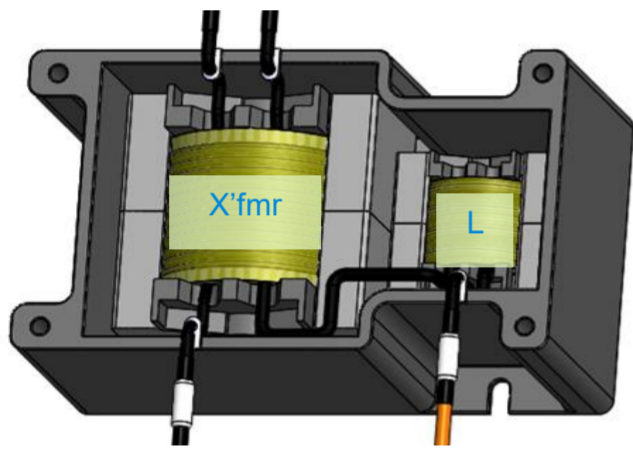


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# Next Generation High Integration Magnetics Design

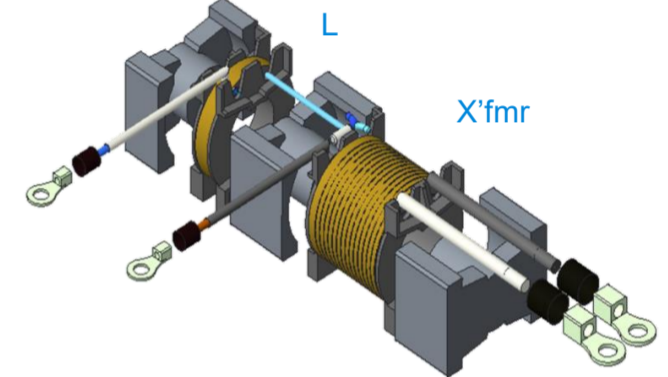
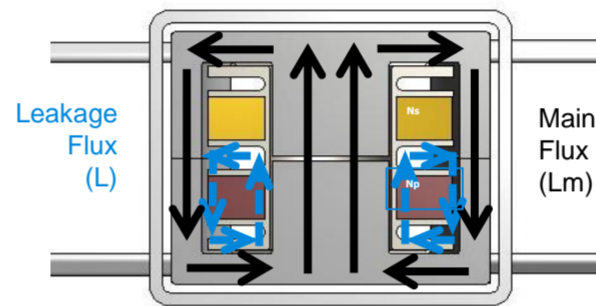
## 1 Package level integration Transformer + Choke

- Flexibility & customized design
- Available wide inductance range
- Better thermal performance
- High quality potting process



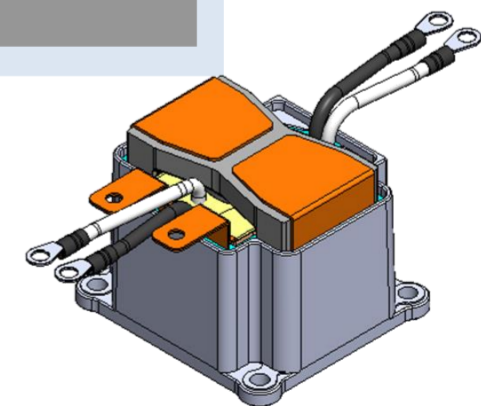
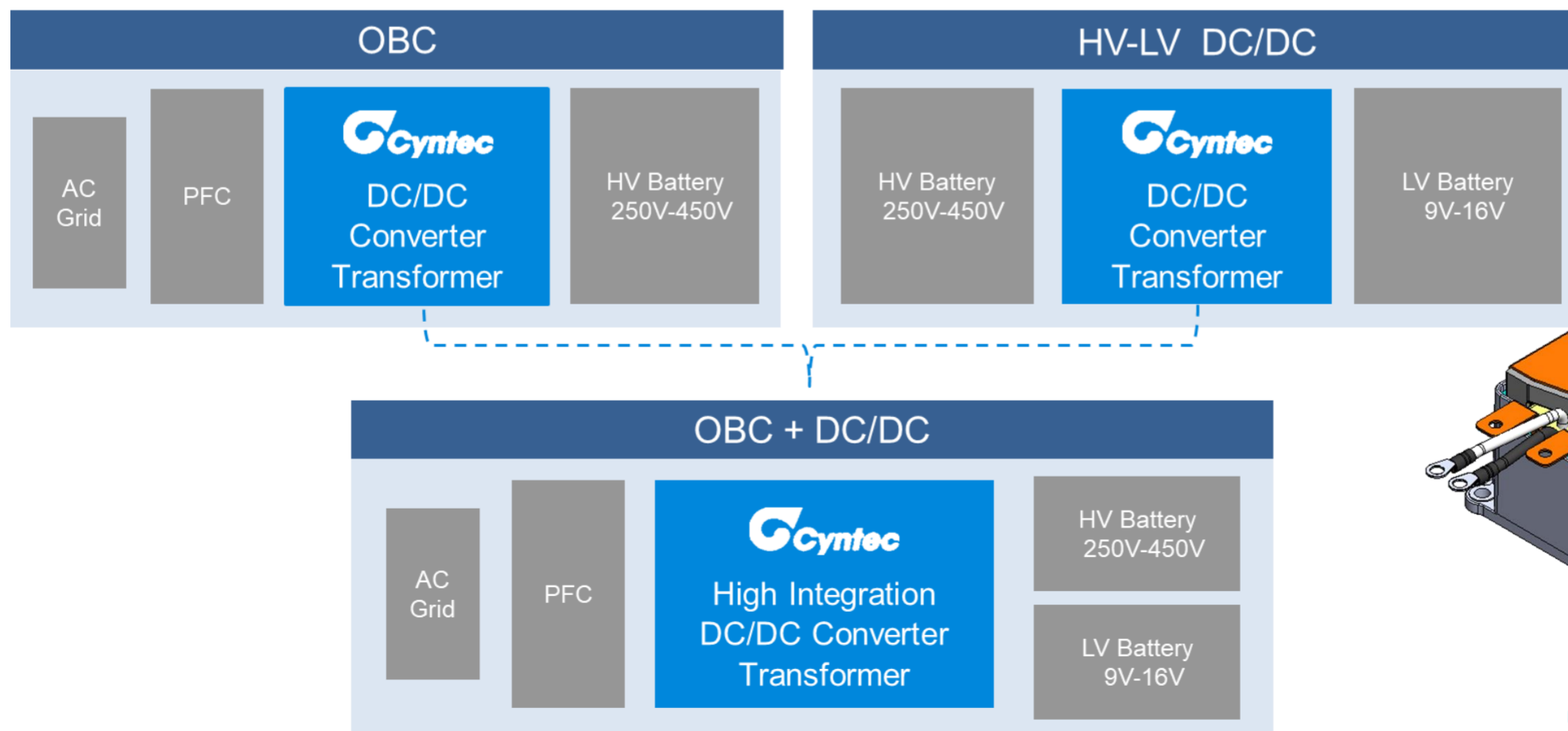
## 2 Magnetic integration Size reduction via core sharing

- Size reduction via core sharing
- Leakage as inductor possible
- Compared with discrete design, size (~25% ↓) and weight (~25% ↓)

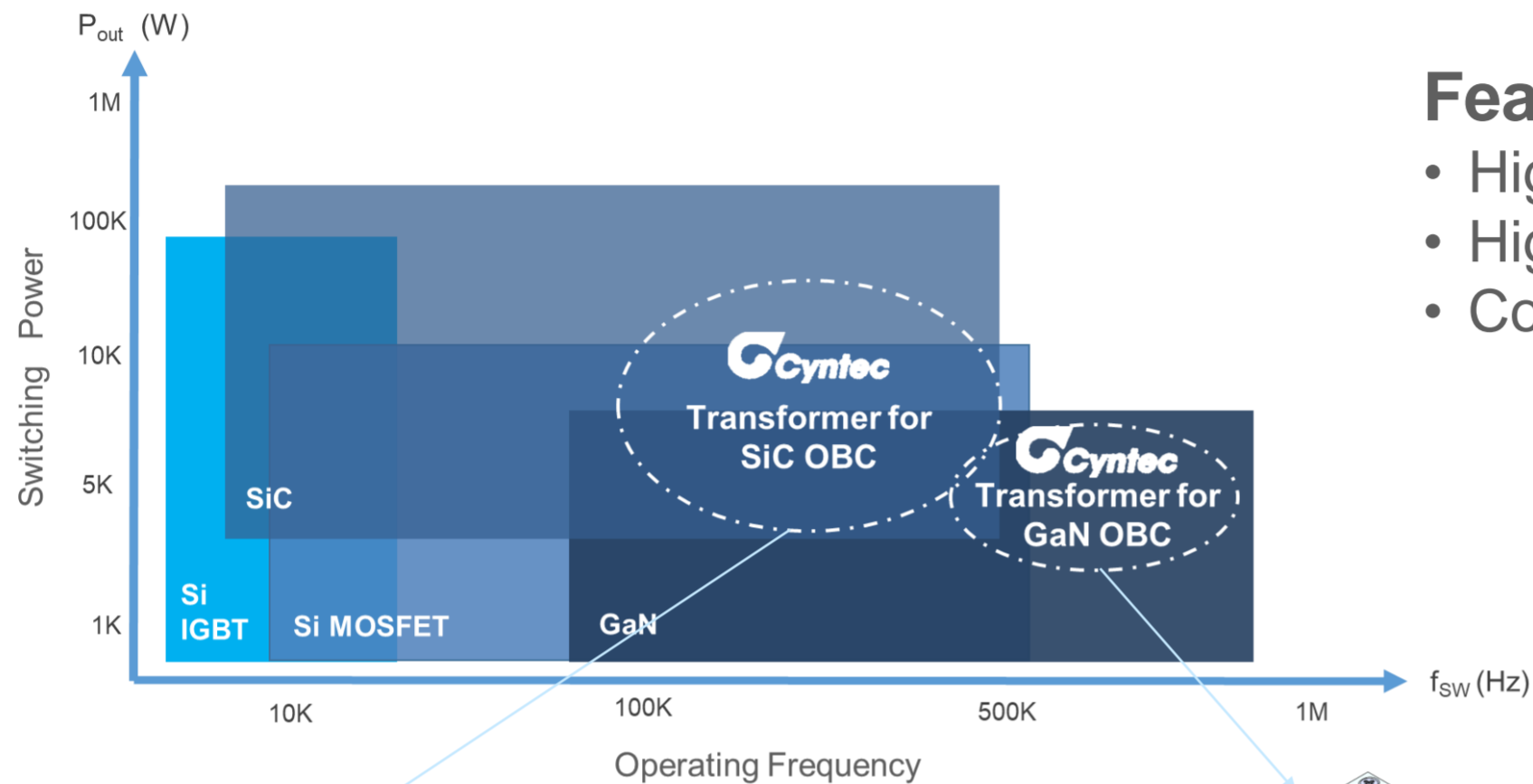


## 3 Function integration Single transformer for HV and LV battery

- Single transformer for HV and LV battery
- Compared with separated OBC and DC/DC structure design, size (~35% ↓) and weight (~30% ↓)

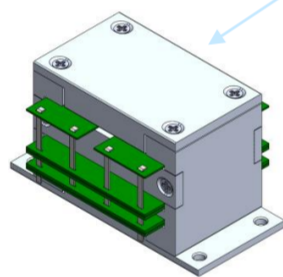


# High Power Density Magnetics for SiC / GaN Based OBC

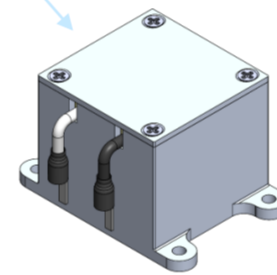


## Feature

- High power density
- High conversion efficiency
- Cost / Performance optimized



**Transformer for 6.6kW SiC CLLC OBC**

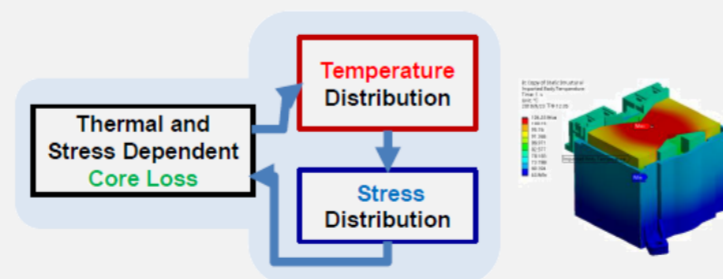


**Transformer for 6.6kW GaN CLLC OBC**

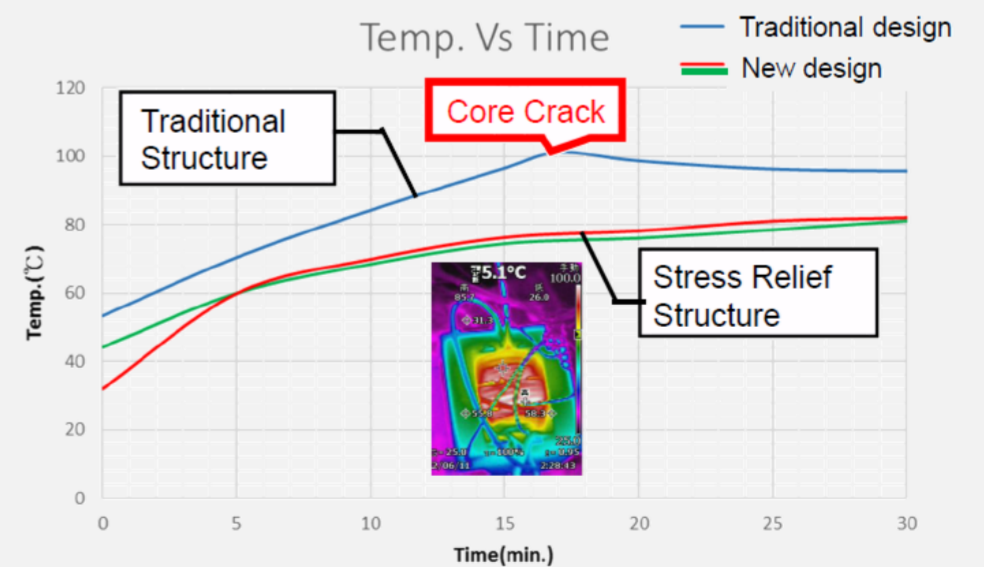
## Multi-physics Stress Relief Design

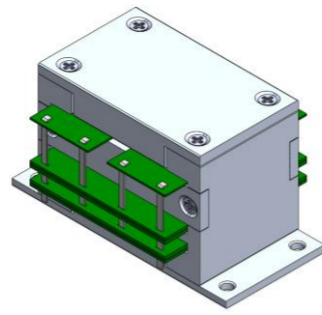
$$P_{CV} = C_m f^x \Delta B_m^y (T, \sigma)$$

Core Loss      Temperature      Stress

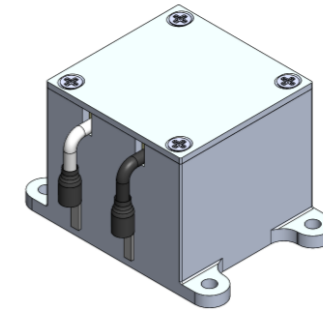


- Flux density optimization
- Heat dissipation optimization
- Stress-relieving structure





## Transformer for 6.6kW SiC CLLLC OBC



## Transformer for 6.6kW GaN CLLLC OBC

### 1 Miniaturization

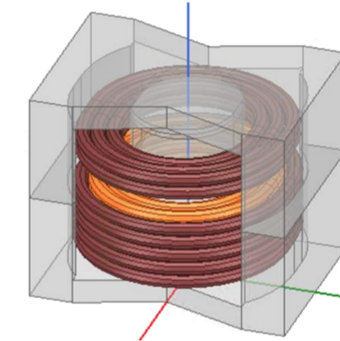
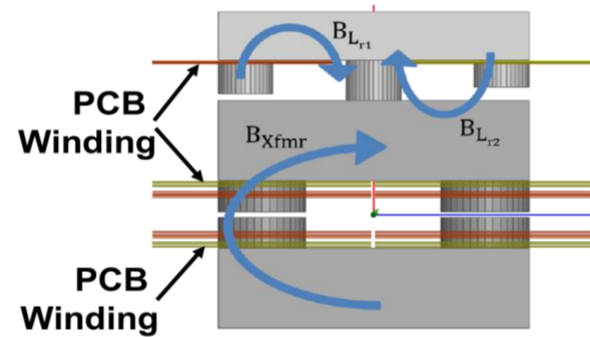
**40%** size reduction  
Magnetic circuit integration  
(99.0 x 66.5 x 56.0 mm<sup>3</sup> Max.)

**50%** size reduction  
Leakage as resonant inductors  
(74.0 X 52.0 X 47.0 mm<sup>3</sup> Max.)

### 2 Lower winding loss & core loss

- Avoid air gap fringing to reduce winding loss
- Fluxing cancelling for lower core loss

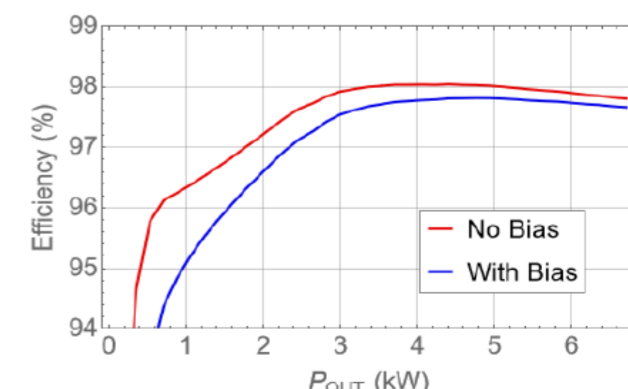
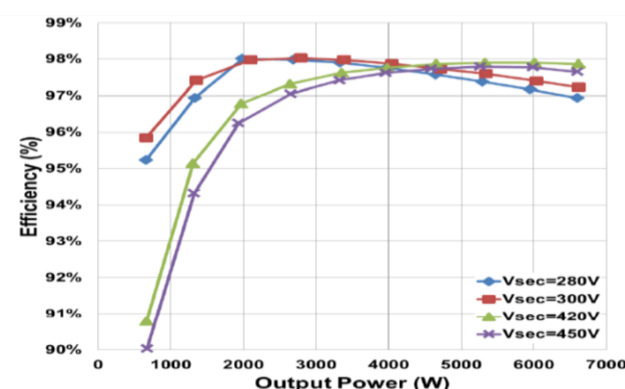
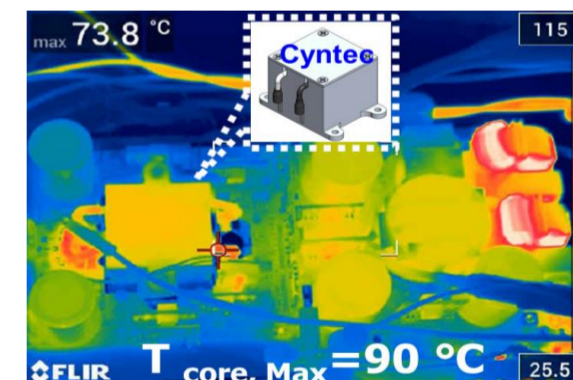
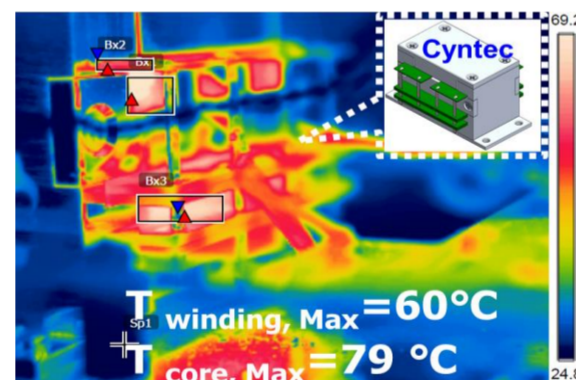
- Suitable litz wire bundle arrangement & winding away from gap to reduce winding loss
- Optimize flux density to reduce core loss



### 3 Effective heat dissipation & higher conversion efficiency

**>98%** Peak efficiency

**>98%** Peak efficiency



# Making Things Smaller and Smarter

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